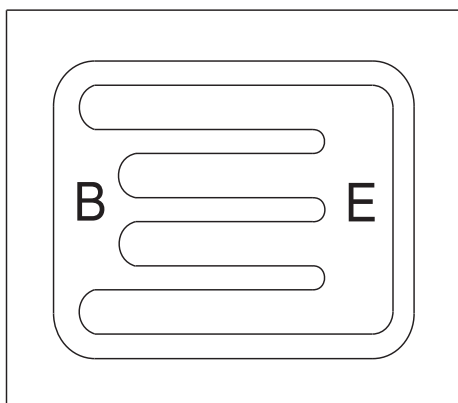


PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	80 x 99 MILS
Die Thickness	12.5 MILS
Base Bonding Pad Area	12 x 32 MILS
Emitter Bonding Pad Area	13 x 48 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Cr/Ni/Ag 16,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

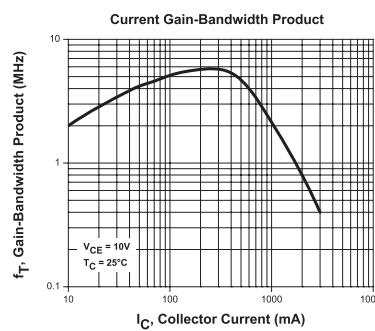
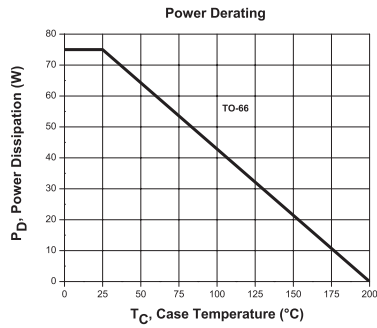
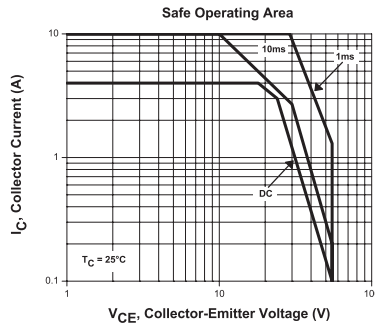
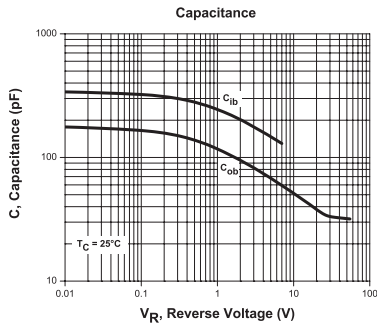
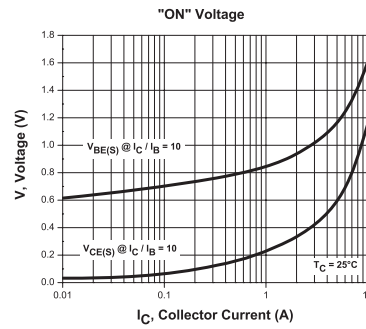
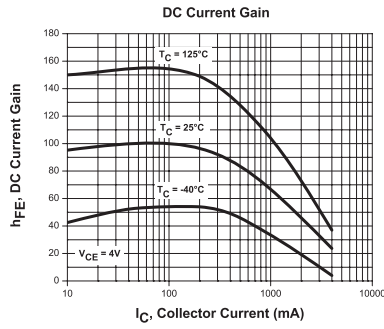
1,450

PRINCIPAL DEVICE TYPES

2N3054A
CJD41C
TIP41C

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R4 (17-August 2006)



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